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JP9227967A: PRODUCTION OF HIGH-PURITY COBALT AND HIGH-PURITY COBALT SPUTTERING TARGET

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IPC Class: **C22B 023/06; C23C 014/14; C23C 014/34; C25C 001/08; H01L 021/3205;**

Abstract:

Problem to be solved: To provide a process capable of stably and easily producing high-purity cobalt of 5N level which is suitable for applications, such as targets, and contains alkaline metal elements, radioactive elements, transition metal elements and impurities, such as gaseous components only to the min. possible extent.

Solution: An aq. cobalt chloride soln. which contains impurities including at least Fe and/or Ni and has a hydrochloric acid concn. of 7 to 12N is brought into contact with an anion exchange resin to have the cobalt adsorbed thereon and, thereafter, the cobalt is eluted by using the hydrochloric acid of 1 to 6N. After the resulted eluate is evaporated to be dried up or is thickened, the aq. soln. of the high-purity cobalt chloride of pH=0 to 6 is obtd. Further, the org. matter in the soln. is removed by active carbon and the electrodeposited cobalt is obtd. by electrolytic refining using the aq. soln. as an electrolyte. The org. matter in the soln. derived from the anion exchange resin is removed by the active carbon.

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Foreign References: **none**

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